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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)

Shunpei YAMAZAKI et al.)

Serial No. 09/699,466)

Filed: October 31, 2000)

For: METHOD FOR FABRICATING A)

SEMICONDUCTOR DEVICE)

Art Unit: 2829

Examiner: A Sakar

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on June 23, 2003.

*Add in Stamp*AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Official Action dated January 22, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 35-45 as follows.

1. (Amended) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film on an insulating surface;

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface;

performing a plasma treatment to the semiconductor island;

forming a first gate insulating film over the semiconductor island wherein the first gate insulating film comprises silicon oxide;

forming a second gate insulating film over the first gate insulating film wherein the second gate insulating film comprises silicon oxide nitride;

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